

Please amend the claims as follows:

C1 2
1. (twice amended) A thin film transistor, comprising:
a stepped substrate provided with a sidewall between upper and lower ^{portions} [portion]
thereof;
an active layer formed on the stepped substrate;
a gate insulation film formed on a lower portion and a sidewall of the active layer
contiguous the [lower portion] and ^{said} sidewall of the stepped substrate, respectively;
an insulating film formed on a lower portion and a sidewall of the gate ^{insulation} [insulating film]
contiguous the [lower portion] and ^{said} sidewall of the stepped substrate, respectively;
a gate electrode formed on the gate insulation film corresponding to the sidewalls of
the substrate and the insulation film; and
impurity regions in the active layer corresponding to the upper and lower portions of
the substrate.

REMARKS

Claims 1, 2, and 4 to 6 remain in this application.

Claims 1 to 6 stand rejected under 35 U.S.C. 112, first paragraph, as lacking support for a single Z-shaped substrate. Consequently, this language has been deleted from claim 1. In addition, claim 3 has been canceled.